

## **MJE200**

### **Feature**

- Low Collector-Emitter Saturation Voltage
- High Current Gain Bandwidth Product :  $f_T$ =65MHz @  $I_C$ =100mA (Min.)
- Complement to MJE210



## **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>EBO</sub>	Emitter- Base Voltage	8	V
Ic	Collector Current	5	Α
Pc	Collector Dissipation (T <sub>C</sub> =25°C)	15	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	25		V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =40V, I <sub>E</sub> =0		100	nA
	nZSU.	V <sub>CB</sub> =40V, I <sub>E</sub> =0 @ T <sub>J</sub> =125°C		100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>BE</sub> =8V, I <sub>C</sub> =0		100	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =1V, I <sub>C</sub> =500mA	70		
		$V_{CE}=1V$ , $I_{C}=2A$	45	180	
		$V_{CE}=2V$ , $I_{C}=5A$	10		2400
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA	10	0.3	V
		I <sub>C</sub> =2A, I <sub>C</sub> =200mA	CAT	0.75	V
		I <sub>C</sub> =5A, I <sub>B</sub> =1A	Court Wi	1.8	V
V <sub>BE</sub> (sat)	Base- Emitter Saturation Voltage	I <sub>C</sub> =5A, I <sub>B</sub> =1A		2.5	V
V <sub>BE</sub> (on)	Base-Emitter ON Voltage	V <sub>CE</sub> =1V, I <sub>C</sub> =2A		1.6	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =100mA	65		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=0.1MHz		80	pF

# **Typical Characteristics**

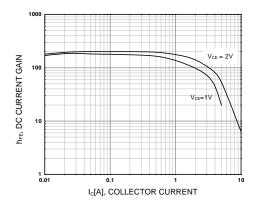


Figure 1. DC current Gain

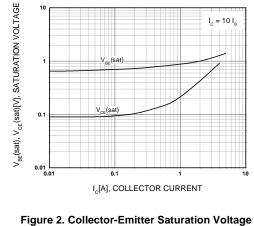


Figure 2. Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage

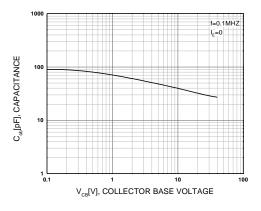


Figure 3. Collector Output Capacitance

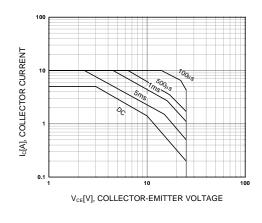


Figure 4. Safe Operating Area

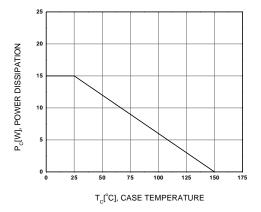
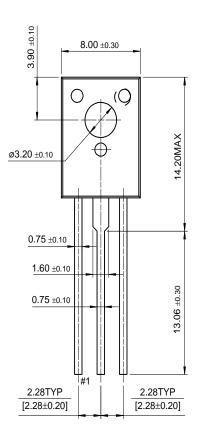


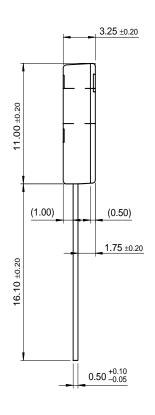
Figure 5. Power Derating

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# **Package Demensions**

TO-126







Dimensions in Millimeters

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